

CLAIM AMENDMENTS

Please amend claims 21 and 22 as follows:

1. (Previously Presented) A gauge apparatus for use in a semiconductor fabrication system, said apparatus comprising:

an electrostatic chuck associated with a semiconductor fabrication system, wherein said electrostatic is moveable from a first position to a second position; and

a gauge for measuring a gap between a baffle plate and a chamber wall, and preventing damage to said chamber wall by said baffle plate during a movement of said electrostatic chuck during a semiconductor fabrication operation of said semiconductor fabrication system, wherein said gauge is located proximate to said electrostatic chuck at said second position of said electrostatic chuck.

2. (Original) The apparatus of claim 1 wherein said semiconductor fabrication operation comprises a wet cleaning semiconductor operation.

3. (Original) The apparatus of claim 1 wherein said gauge is adapted for use in leveling said electrostatic chuck.

4. (Original) The apparatus of claim 1 wherein said gauge comprises a horizontal gap gauge.

5. (Original) The apparatus of claim 1 wherein said gauge is adapted for use in preventing polymer peeling of said chamber wall.

6. (Original) The apparatus of claim 1 wherein said gauge comprises a leveling gauge.

7. (Original) The apparatus of claim 1 wherein said semiconductor fabrication system comprises dual-rotate-magnet (DRM).

8. (Original) The apparatus of claim 7 wherein said semiconductor fabrication system comprises a focus ring.

9. (Original) The apparatus of claim 8 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

10. (Original) The apparatus of claim 8 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a horizontal movement.

11. (Original) A method for preventing damage to a chamber wall by a baffle plate in a semiconductor fabrication system during a semiconductor fabrication operation, said method comprising the steps of:

moving an electrostatic chuck associated with said semiconductor fabrication system during said semiconductor fabrication operation; and

measuring a gap between said baffle plate and said chamber wall utilizing a gauge integrated with said semiconductor fabrication system, in response to moving said electrostatic chuck to thereby prevent damage to said chamber wall by said baffle plate.

12. (Original) The method of claim 11 wherein said semiconductor fabrication operation comprises a wet cleaning semiconductor operation.

13. (Original) The method of claim 11 wherein said gauge is adapted for use in leveling said electrostatic chuck.

14. (Original) The method of claim 11 wherein said gauge comprises a horizontal gap gauge.

15. (Original) The method of claim 11 wherein said gauge is adapted for use in preventing polymer peeling of said chamber wall.

16. (Original) The method of claim 11 wherein said gauge comprises a leveling gauge.

17. (Original) The method of claim 11 wherein said semiconductor fabrication system comprises dual-rotate-magnet (DRM).

18. (Original) The method of claim 17 wherein said semiconductor fabrication system comprises a focus ring.

19. (Original) The method of claim 18 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

20. (Original) The method of claim 18 wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a horizontal movement.

21. (Currently Amended) A gauge apparatus for use in a semiconductor fabrication system, said apparatus comprising:

an electrostatic chuck associated with a semiconductor fabrication system comprising a dual-rotate-magnet (DRM) and a focus ring, wherein said electrostatic is moveable from a first position to a second position; and

a horizontal gap gauge for accurately measuring a gap between a baffle plate and a chamber wall, and preventing polymer peeling of damage to said chamber wall by said baffle plate during a movement of said electrostatic chuck during a semiconductor fabrication operation of said semiconductor fabrication system in order to assist in leveling said electrostatic chuck, wherein said gauge is located proximate to said electrostatic chuck at said second position of said electrostatic chuck, wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.

22. (Currently Amended) A method for preventing damage to a chamber wall by a baffle plate in a semiconductor fabrication system during a semiconductor fabrication operation, said method comprising the steps of:

associating an electrostatic chuck with a semiconductor fabrication system comprising a dual-rotate-magnet (DRM) and a focus ring, wherein said electrostatic is moveable from a first position to a second position; and

utilizing a leveling gauge to measure ~~measuring~~ a gap between formed between a baffle plate and a chamber wall and preventing damage to said chamber wall by said baffle plate during a movement of said electrostatic chuck during a semiconductor fabrication operation of said semiconductor fabrication system utilizing a gauge that is located proximate to said electrostatic chuck at said second position of said electrostatic chuck, wherein said movement of said electrostatic chuck during said semiconductor fabrication operation comprises a vertical movement.